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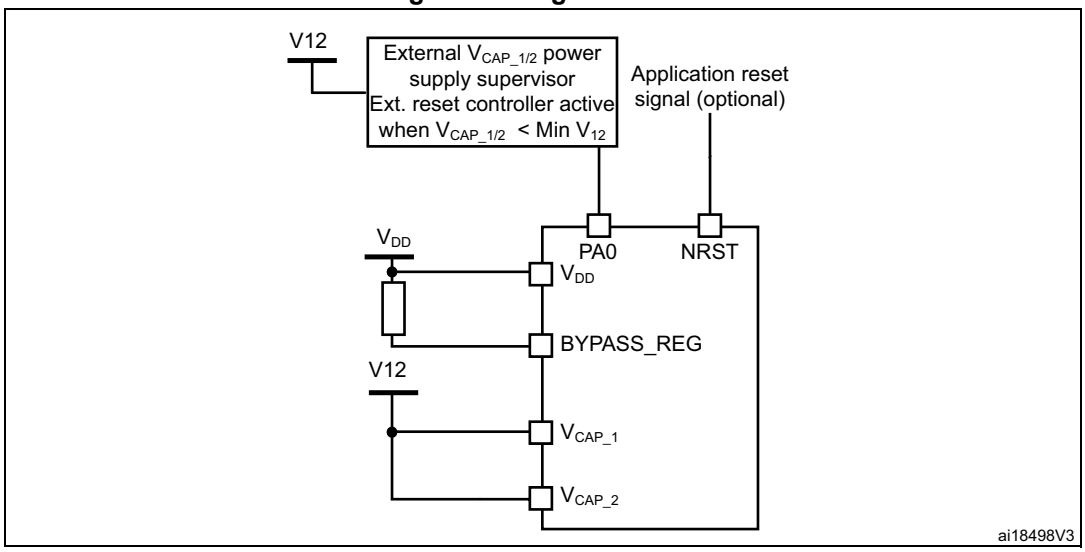
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	140
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f722ict6

Figure 11. Regulator OFF



The following conditions must be respected:

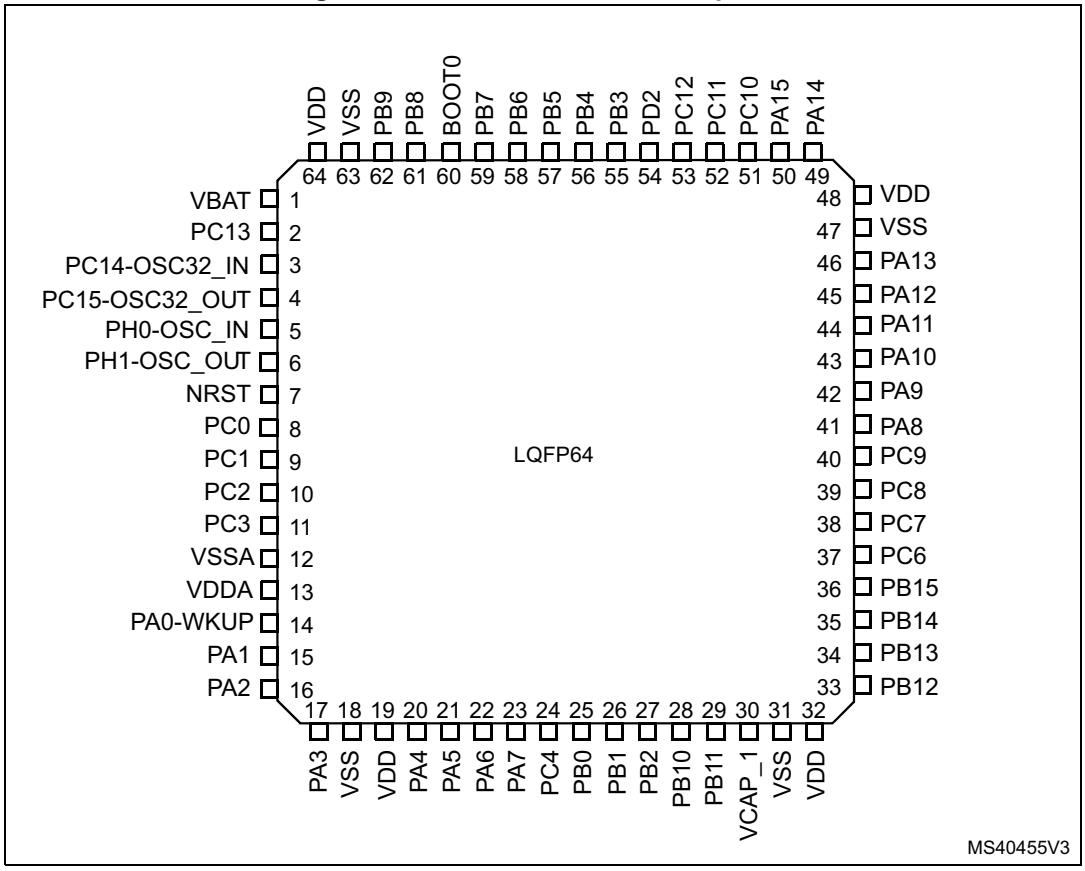
- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see *Figure 12*).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see *Figure 13*).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application.

Note: On the LQFP64 pin package, the V_{CAP_2} is not available.

3 Pinouts and pin description

Figure 14. STM32F722xx LQFP64 pinout



1. The above figure shows the package top view.

Table 10. STM32F722xx and STM32F723xx pin and ball definition (continued)

Pin Number										Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F722xx					STM32F723xx										
LQFP64	LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP100	UFBGA176	UFBGA144	LQFP144	LQFP176						
-	44	67	P11	77	K4	P11	L8	67	77	PE14	I/O	FT	-	TIM1_CH4, SPI4_MOSI, SAI2_MCK_B, FMC_D11,, EVENTOUT	-
-	45	68	R11	78	F4	R11	M8	68	78	PE15	I/O	FT	-	TIM1_BKIN, FMC_D12, EVENTOUT	-
28	46	69	R12	79	G3	R12	M9	69	79	PB10	I/O	FTf	(4)	TIM2_CH3, I2C2_SCL, SPI2_SCK/I2S2_CK, USART3_TX, OTG_HS_ULPI_D3, EVENTOUT	-
29	47	70	R13	80	H3	R13	M10	70	80	PB11	I/O	FTf	(4)	TIM2_CH4, I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, EVENTOUT	-
30	48	71	M10	81	J3	M10	H7	71	81	VCAP_1	S	-	-	-	-
31	49	-	-	-	K3	-	-	-	-	VSS	S	-	-	-	-
32	50	72	N10	82	K2	N10	G7	72	82	VDD	S	-	-	-	-
-	-	-	M11	83	-	M11	-	-	83	PH6	I/O	FT	-	I2C2_SMBA, SPI5_SCK, TIM12_CH1, FMC_SDNE1, EVENTOUT	-
-	-	-	N12	84	-	N12	-	-	84	PH7	I/O	FTf	-	I2C3_SCL, SPI5_MISO, FMC_SDCKE1, EVENTOUT	-
-	-	-	M12	85	-	M12	-	-	85	PH8	I/O	FTf	-	I2C3_SDA, FMC_D16, EVENTOUT	-

Table 10. STM32F722xx and STM32F723xx pin and ball definition (continued)

Pin Number										Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F722xx					STM32F723xx										
LQFP64	LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP100	UFBGA176	UFBGA144	LQFP144	LQFP176						
39	65	98	G14	117	D2	G14	F11	98	117	PC8	I/O	FT	-	TRACED1, TIM3_CH3, TIM8_CH3, UART5_RTS, USART6_CK, SDMMC1_D0, EVENTOUT	-
40	66	99	F14	118	D1	F14	E11	99	118	PC9	I/O	FTf	-	MCO2, TIM3_CH4, TIM8_CH4, I2C3_SDA, I2S_CKIN, UART5_CTS, QUADSPI_BK1_IO0, SDMMC1_D1, EVENTOUT	-
41	67	100	F15	119	D3	F15	E12	100	119	PA8	I/O	FTf	-	MCO1, TIM1_CH1, TIM8_BKIN2, I2C3_SCL, USART1_CK, OTG_FS_SOF, EVENTOUT	-
42	68	101	E15	120	C3	E15	D12	101	120	PA9	I/O	FT	-	TIM1_CH2, I2C3_SMBA, SPI2_SCK/I2S2_CK, USART1_TX, EVENTOUT	OTG_FS_VBUS
43	69	102	D15	121	C2	D15	D11	102	121	PA10	I/O	FT	-	TIM1_CH3, USART1_RX, OTG_FS_ID, EVENTOUT	-
44	70	103	C15	122	C1	C15	C12	103	122	PA11	I/O	FT	-	TIM1_CH4, USART1_CTS, CAN1_RX, OTG_FS_DM, EVENTOUT	-
45	71	104	B15	123	B2	B15	B12	104	123	PA12	I/O	FT	-	TIM1_ETR, USART1_RTS, SAI2_FS_B, CAN1_TX, OTG_FS_DP, EVENTOUT	-
46	72	105	A15	124	B1	A15	A12	105	124	PA13(JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-

Table 12. STM32F722xx and STM32F723xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1	I2C1/2/3/USART1	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5	SPI2/I2S2/SPI3/I2S3/SPI3/I2S3/SAI1/UART4	SPI2/I2S2/SPI3/I2S3/USART1/2/3/UART5	SAI2/USART6/UART4/5/7/8/OTG1_FS	CAN1/TIM12/13/14/QUADSPI/FMC/OTG2_HS	SAI2/QUADSPI/SDMMC2/OTG2_HS/OTG1_FS	SDMMC2	UART7/FMC/SDMMC1/OTG2_FS	SYS
Port B	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/I2S2_WS	-	-	-	CAN1_TX	SDMMC2_D5	-	SDMMC1_D5	EVENTOUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/I2S2_CK	-	USART3_TX	-	-	OTG_HS_ULPI_D3	-	-	EVENTOUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	OTG_HS_ULPI_D4	-	-	EVENTOUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS/I2S2_WS	-	USART3_CK	-	-	OTG_HS_ULPI_D5	-	OTG_HS_ID	EVENTOUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK/I2S2_CK	-	USART3_CTS	-	-	OTG_HS_ULPI_D6	-	-	EVENTOUT
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	-	SPI2_MISO	-	USART3_RTS	-	TIM12_CH1	SDMMC2_D0	-	OTG_HS_DM	EVENTOUT
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI/I2S2_SD	-	-	-	TIM12_CH2	SDMMC2_D1	-	OTG_HS_DP	EVENTOUT
Port C	PC0	-	-	-	-	-	-	-	-	SAI2_FS_B	-	OTG_HS_ULPI_STP	-	FMC_SDNWE	EVENTOUT
	PC1	TRACED0	-	-	-	-	SPI2_MOSI/I2S2_SD	SAI1_SD_A	-	-	-	-	-	-	EVENTOUT
	PC2	-	-	-	-	-	SPI2_MISO	-	-	-	-	OTG_HS_ULPI_DIR	-	FMC_SDNE0	EVENTOUT
	PC3	-	-	-	-	-	SPI2_MOSI/I2S2_SD	-	-	-	-	OTG_HS_ULPI_NXT	-	FMC_SDCKE0	EVENTOUT

Table 12. STM32F722xx and STM32F723xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1	I2C1/2/3/UART1	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5	SPI2/I2S2/SPI3/I2S3/SPI3/I2S3/SAI1/UART4	SPI2/I2S2/SPI3/I2S3/USART1/2/3/UART5	SAI2/USART6/UART4/5/7/8/OTG1_FS	CAN1/TIM12/13/14/QUADSPI/FMC/OTG2_HS	SAI2/QUADSPI/SDMMC2/OTG2_HS/OTG1_FS	SDMMC2	UART7/FMC/SDMMC1/OTG2_FS	SYS
Port H	PH8	-	-	-	-	I2C3_SDA	-	-	-	-	-	-	-	FMC_D16	EVENTOUT
	PH9	-	-	-	-	I2C3_SMBA	-	-	-	-	TIM12_CH2	-	-	FMC_D17	EVENTOUT
	PH10	-	-	TIM5_CH1	-	-	-	-	-	-	-	-	-	FMC_D18	EVENTOUT
	PH11	-	-	TIM5_CH2	-	-	-	-	-	-	-	-	-	FMC_D19	EVENTOUT
	PH12	-	-	TIM5_CH3	-	-	-	-	-	-	-	-	-	FMC_D20	EVENTOUT
	PH13	-	-	-	TIM8_CH1N	-	-	-	-	UART4_TX	CAN1_TX	-	-	FMC_D21	EVENTOUT
	PH14	-	-	-	TIM8_CH2N	-	-	-	-	UART4_RX	CAN1_RX	-	-	FMC_D22	EVENTOUT
	PH15	-	-	-	TIM8_CH3N	-	-	-	-	-	-	-	-	FMC_D23	EVENTOUT
Port I	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS/I2S2_WS	-	-	-	-	-	-	FMC_D24	EVENTOUT
	PI1	-	-	-	TIM8_BKIN2	-	SPI2_SCK/I2S2_CK	-	-	-	-	-	-	FMC_D25	EVENTOUT
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	-	-	-	-	-	-	FMC_D26	EVENTOUT
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI/I2S2_SD	-	-	-	-	-	-	FMC_D27	EVENTOUT
	PI4	-	-	-	TIM8_BKIN	-	-	-	-	-	-	SAI2_MCK_A	-	FMC_NBL2	EVENTOUT
	PI5	-	-	-	TIM8_CH1	-	-	-	-	-	-	SAI2_SCK_A	-	FMC_NBL3	EVENTOUT
	PI6	-	-	-	TIM8_CH2	-	-	-	-	-	-	SAI2_SD_A	-	FMC_D28	EVENTOUT

4 Memory mapping

The memory map is shown in *Figure 24*.

Figure 24. Memory map

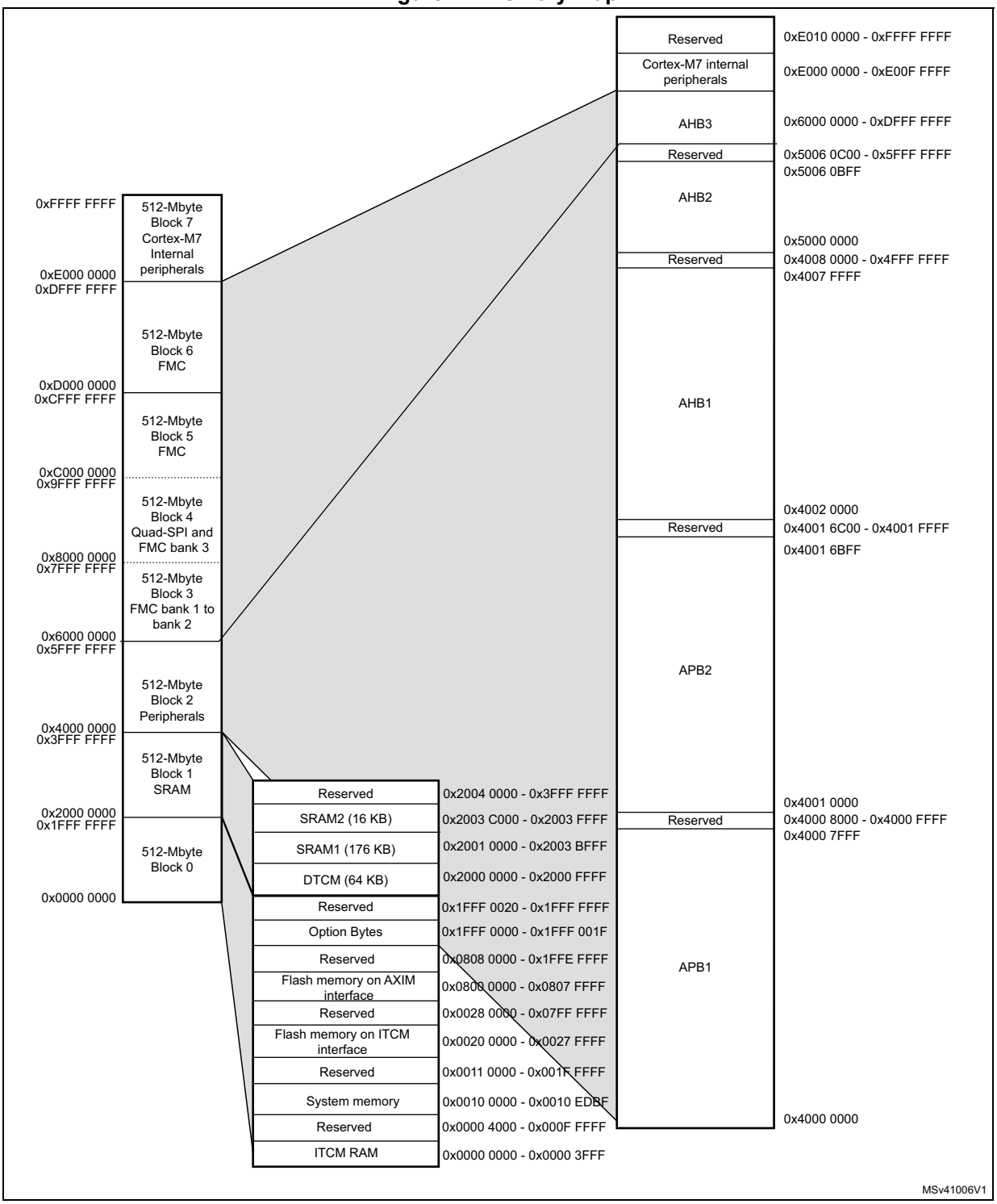


Table 13. STM32F722xx and STM32F723xx register boundary addresses(1) (continued)

Bus	Boundary address	Peripheral
	0x4001 8000- 0x4001 FFFF	Reserved
APB2	0x4001 7C00 - 0x4001 7FFF	OTG PHY HS Controller(2)
	0x4001 6000- 0x4001 7BFF	Reserved
	0x4001 5C00 - 0x4001 5FFF	SAI2
	0x4001 5800 - 0x4001 5BFF	SAI1
	0x4001 5400 - 0x4001 57FF	Reserved
	0x4001 5000 - 0x4001 53FF	SPI5
	0x4001 4C00 - 0x4001 4FFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4
	0x4001 3000 - 0x4001 33FF	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	SDMMC1
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1 - ADC2 - ADC3
	0x4001 1C00- 0x4001 1FFF	SDMMC2
	0x4001 1800 - 0x4001 1BFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
	0x4001 0000 - 0x4001 03FF	TIM1

5.3.15 USB HS PHY external resistor characteristics (on STM32F723xx devices)

Table 52. USB HS PHY external resistor characteristics (on STM32F723xx devices)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
REXT	External calibration resistor connected (to GND) from OTG_HS_REXT	Required if using USB HS PHY	2.97	3.00	3.03	kΩ

5.3.16 Memory characteristics

Flash memory

The characteristics are given at TA = –40 to 105 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 53. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	6.7	-	mA
		Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	9.2	-	
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12.6	-	

Table 54. Flash memory programming

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	346	418	ms
		Program/erase parallelism (PSIZE) = x 16	-	252	312	
		Program/erase parallelism (PSIZE) = x 32	-	208	265	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1953	2500	ms
		Program/erase parallelism (PSIZE) = x 16	-	1252	1639	
		Program/erase parallelism (PSIZE) = x 32	-	927	1322	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1027	1298	ms
		Program/erase parallelism (PSIZE) = x 16	-	675	840	
		Program/erase parallelism (PSIZE) = x 32	-	505	682	

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 60. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

5.3.19 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in *Table 61*.

Table 61. I/O current injection susceptibility(1)

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0, PDR_ON, BYPASS_REG, OTG_HS_REXT	-0	0	mA
	Injected current on NRST	-0	NA	
	Injected current on PF9, PF10, PH0_OSCIN, PH1_OSCOUT, PC0, PC1, PC2, PC3, PB14(2), PB15(2)	-0	NA	
	Injected current on any other FT or FTf pins	-5	NA	
	Injected current on any other pins	-5	+5	

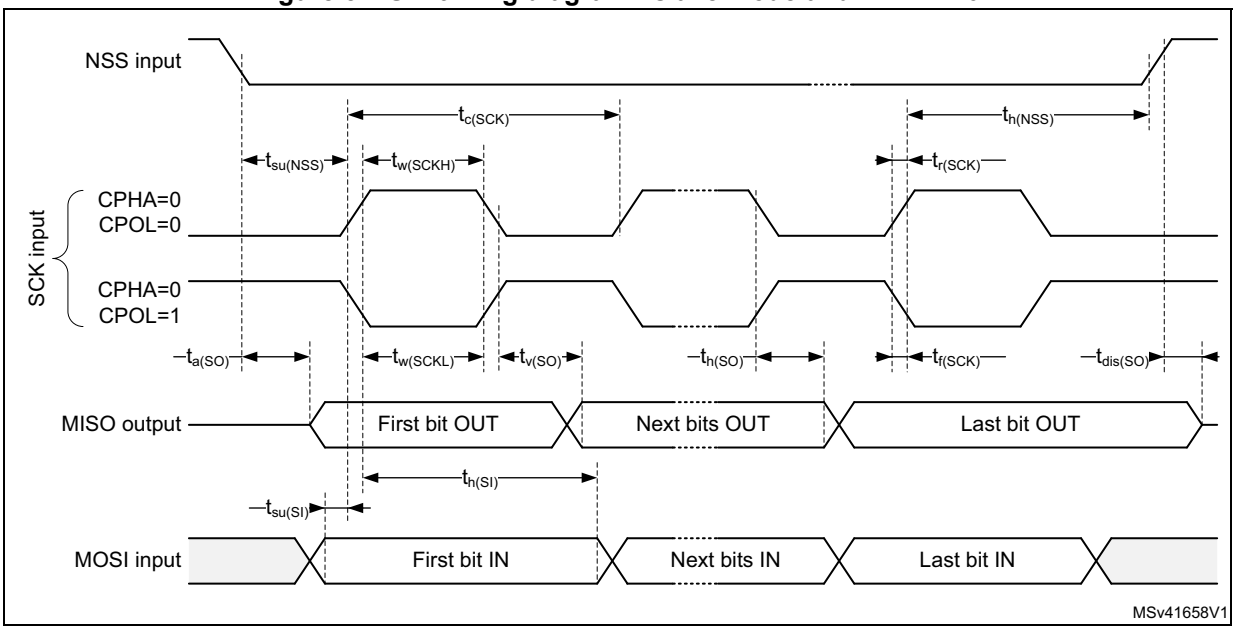
1. NA = not applicable.

Table 82. SPI dynamic characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
tsu(MI)	Data input setup time	Master mode	4	-	-	ns
tsu(SI)		Slave mode	3.5	-	-	
th(MI)	Data input hold time	Master mode	3	-	-	
th(SI)		Slave mode	1	-	-	
ta(SO)	Data output access time	Slave mode	7	9	21	
tdis(SO)	Data output disable time	Slave mode	5	7	12	
tv(SO)	Data output valid time	Slave mode 2.7≤VDD≤3.6V	-	6.5	10	
		Slave mode 1.71≤VDD≤3.6V	-	6.5	13.5	
tv(MO)		Master mode	-	2	3	
th(SO)	Data output hold time	Slave mode 1.71≤VDD≤3.6V	4.5	-	-	
th(MO)		Master mode	0	-	-	

1. Guaranteed by characterization results.
2. Excepting SPI1 with SCK IO=PA5. In this configuration, the maximum achievable frequency is 40 MHz.
3. Maximum frequency of the slave transmitter is determined by sum of Tv(SO) and Tsu(MI) intervals which has to fit into SCK level phase preceding the SCK sampling edge.This value can be achieved when it communicates with a Master having Tsu(MI)=0 while signal Duty(SCK)=50%.

Figure 52. SPI timing diagram - slave mode and CPHA = 0



I²S interface characteristics

Unless otherwise specified, the parameters given in *Table 83* for the I²S interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 83. I²S dynamic characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256 x 8K	256xFs(2)	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	-	3	ns
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	5	-	
$t_{h(WS)}$	WS hold time	Slave mode	2	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	2.5	-	
$t_{su(SD\_SR)}$		Slave receiver	2.5	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	3.5	-	
$t_{h(SD\_SR)}$		Slave receiver	2	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	12	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	3	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	5	-	
$t_{h(SD\_MT)}$		Master transmitter (after enable edge)	0	-	

1. Guaranteed by characterization results.
2. 256xFs maximum is 49.152 MHz (APB1 Maximum frequency).

Note: Refer to RM0385 reference manual I2S section for more details on the sampling frequency (F_S).

*f_{MCK}, f_{CK}, and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of (I2SDIV/(2*I2SDIV+ODD) and a maximum value of (I2SDIV+ODD)/(2*I2SDIV+ODD). F_S maximum value is supported for each mode/condition.*

USB OTG full speed (FS) characteristics

This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 85. USB OTG full speed startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB OTG full speed transceiver startup time	1	µs

1. Guaranteed by design.

Table 86. USB OTG full speed DC electrical characteristics

Symbol		Parameter	Conditions	Min.(1)	Typ.	Max.(1)	Unit
Input levels	V_{DDUSB}	USB OTG full speed transceiver operating voltage	-	3.0(2)	-	3.6	V
	V_{DI}(3)	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	V_{CM}(3)	Differential common mode range	Includes V_{DI} range	0.8	-	2.5	
	V_{SE}(3)	Single ended receiver threshold	-	1.3	-	2.0	
Output levels	V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(4)	-	-	0.3	V
	V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(4)	2.8	-	3.6	
R_{PD}		PA11, PA12 (USB_FS_DP/DM)	V_{IN} = V_{DD}	14.25	-	24.8	kΩ
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	V_{IN} = V_{DD}	2.4	5.2	8	
R_{PU}		PA12 (USB_FS_DP)	V_{IN} = V_{SS}, during idle	0.9	1.25	1.575	
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	V_{IN} = V_{SS}, during reception	0.55	0.95	1.35	

1. All the voltages are measured from the local ground potential.
2. The USB OTG full speed transceiver functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DDUSB} voltage range.
3. Guaranteed by design.
4. R_L is the load connected on the USB OTG full speed drivers.

Note: When VBUS sensing feature is enabled, PA9 and PB13 should be left at their default state (floating input), not as alternate function. A typical 200 µA current consumption of the sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 and PB13 when the feature is enabled.

Table 90. Dynamic characteristics: USB ULPI(1)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{SC}	Control in (ULPI_DIR, ULPI_NXT) setup time	-	1.5	-	-	ns
t_{HC}	Control in (ULPI_DIR, ULPI_NXT) hold time	-	1	-	-	
t_{SD}	Data in setup time	-	1.5	-	-	
t_{HD}	Data in hold time	-	1	-	-	
t_{DC}/t_{DD}	Data/control output delay	2.7 V < V_{DD} < 3.6 V, C_L = 20 pF and OSPEEDRy[1:0] = 11	-	6	7.5	
		-	-	9.5	11	
		1.7 V < V_{DD} < 3.6 V, C_L = 15 pF and OSPEEDRy[1:0] = 11	-			

1. Guaranteed by characterization results.

USB high speed (HS) characteristics (Embedded PHY High speed in STM32F723xx devices)

Table 91. USB OTG high speed DC electrical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{hssq}	High speed squelch detection threshold	-	100	-	150	mV
V_{hsdsc}	High speed disconnect detection threshold	-	525	-	625	mV
V_{hsdif}	High speed differential detection threshold	-	100	-	-	mV
V_{hscm}	High speed data signalling common mode voltage range	-	-50	-	500	mV
V_{hsoi}	High speed idle level	-	-10	-	10	mV
V_{hsoh}	High speed data signaling high	-	360	-	440	mV
V_{hsol}	High speed data signaling low	-	-10	-	10	mV
V_{chirpj}	Chirp J level	-	700	-	1100	mV
V_{chirpk}	Chirp K level	-	-900	-	-500	mV

Table 92. USB OTG high speed electrical characteristics

Parameter	Comments	Conditions	Min	Typ	Max	Unit
t_{lr}	Rise time	-	0.5	-	-	ns
t_{lf}	Fall time	-	0.5	-	-	ns
t_{lrfm}	Setup time from INHSDRIVERENABLE=1 to the transition on INHSDATAP/INHSDATAN	-	10	-	-	ns
Z_{drv}	Driver output impedance	-	40.5	-	49.5	Ω

Table 94. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	2Thclk -1	2Thclk +1	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	0	0.5	
$t_{w(NOE)}$	FMC_NOE low time	2Thclk -1	2Thclk +1	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0.5	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{h(BL\_NOE)}$	FMC_BL hold time after FMC_NOE high	0	-	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	Thclk -1.5	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOEx high setup time	Thclk -1.5	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	0	
$t_{w(NADV)}$	FMC_NADV low time	-	Thclk -0.5	

1. C_L = 30 pF.

Table 95. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	7Thclk +1	7Thclk +1	ns
$t_{w(NOE)}$	FMC_NWE low time	5Thclk -1	5Thclk +1	
$t_{w(NWAIT)}$	FMC_NWAIT low time	Thclk -0.5	-	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	5Thclk +1.5	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	4Thclk +1	-	

1. Guaranteed by characterization results.

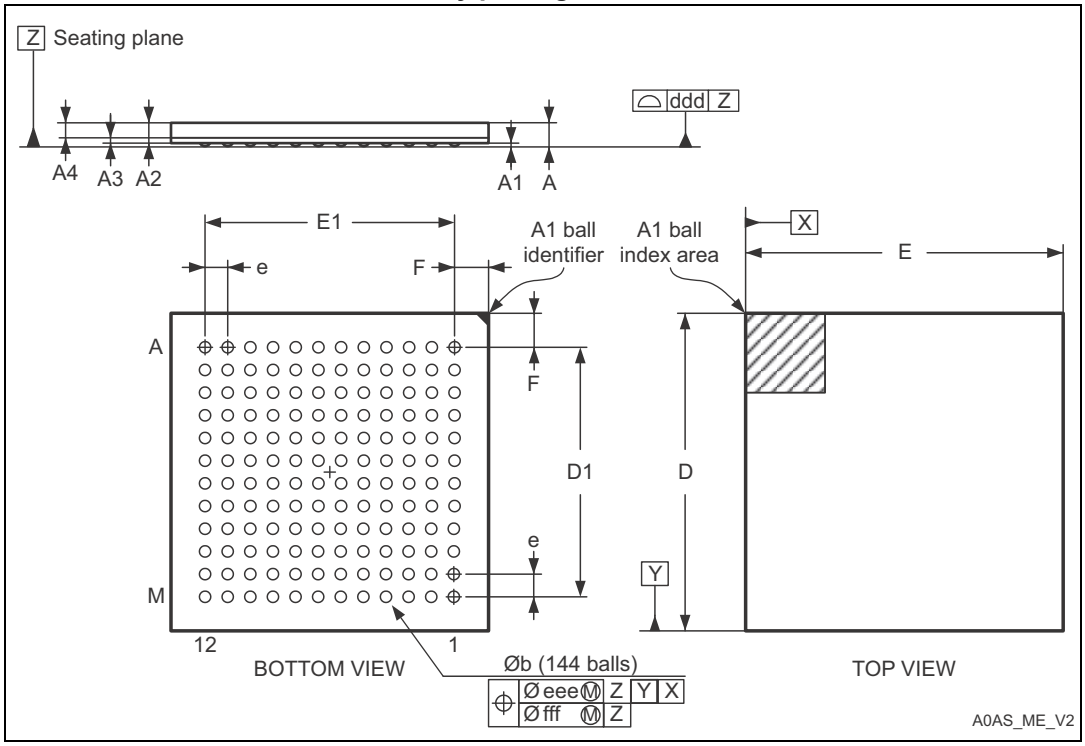
Table 102. Synchronous multiplexed NOR/PSRAM read timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	2Thclk - 0.5	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)		2	
$t_{d(CLKH\_NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	Thclk + 0.5	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	1	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	3	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	Thclk	-	
$t_{d(CLKL-NOEL)}$	FMC_CLK low to FMC_NOE low	-	2	
$t_{d(CLKH-NOEH)}$	FMC_CLK high to FMC_NOE high	Thclk - 0.5	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	2	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{su(ADV-CLKH)}$	FMC_A/D[15:0] valid data before FMC_CLK high	0.5	-	
$t_{h(CLKH-ADV)}$	FMC_A/D[15:0] valid data after FMC_CLK high	4	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3	-	

1. Guaranteed by characterization results.

6.5 UFBGA144 package information

Figure 91. UFBGA144 - 144-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 120. UFBGA144 - 144-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches(1)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.230	0.280	0.320	0.0091	0.0110	0.0126
D	6.950	7.000	7.050	0.2736	0.2756	0.2776
D1	5.450	5.500	5.550	0.2146	0.2165	0.2185
E	6.950	7.000	7.050	0.2736	0.2756	0.2776
E1	5.450	5.500	5.550	0.2146	0.2165	0.2185
e	-	0.500	-	-	0.0197	-
F	0.700	0.750	0.800	0.0276	0.0295	0.0315

Table 120. UFBGA144 - 144-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 92. UFBGA144 - 144-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package recommended footprint

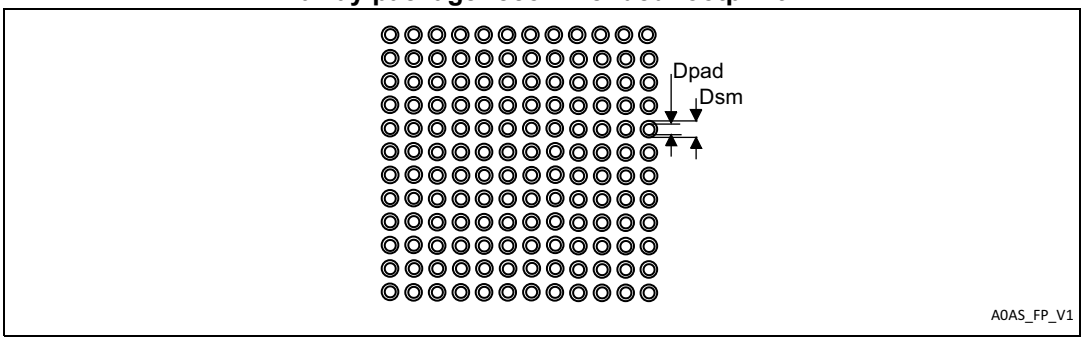


Table 121. UFBGA144 recommended PCB design rules (0.50 mm pitch BGA)

Dimension	Recommended values
Pitch	0.50 mm
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.120 mm

Figure 95. UFBGA176+25, 10 x 10 mm x 0.65 mm, ultra fine-pitch ball grid array package recommended footprint

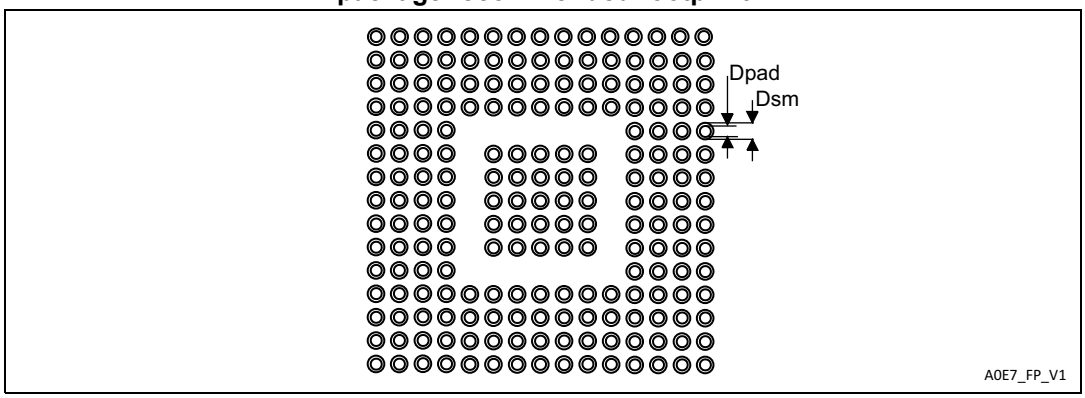


Table 123. UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65 mm
Dpad	0.300 mm
Dsm	0.400 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.300 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Appendix A Recommendations when using internal reset OFF

When the internal reset is OFF, the following integrated features are no longer supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled.
- The brownout reset (BOR) circuitry must be disabled.
- The embedded programmable voltage detector (PVD) is disabled.
- V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD}.
- The over-drive mode is not supported.

A.1 Operating conditions

Table 128. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum Flash memory access frequency with wait states (1)(2)	I/O operation	Possible Flash memory operations
V_{DD} =1.7 to 2.1 V(3)	Conversion time up to 1.2 Msps	20 MHz	180 MHz with 8 wait states and over-drive OFF	– No I/O compensation	8-bit erase and program operations only

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from the Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0-wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V, with the use of an external power supply supervisor (refer to *Section 2.15.1: Internal reset ON*).